

HMIC™ Silicon PIN Diode Switch RoHs Compliant

Rev. V3

Features

- ◆ Ultra Broad Bandwidth: 50MHz to 26GHz
- ◆ 0.9 Insertion Loss , 34dB Isolation at 20GHz
- ◆ 50nS Switching Speed
- ◆ Reliable, Fully Monolithic, Glass Encapsulated Construction
- ◆ +33dBm Power Handling

Description

The MASW-004100-1193 is a SP4T series-shunt broad band switch made with M/A-COM's unique HMIC™ (Heterolithic Microwave Integrated Circuit) process, US Patent 5,268,310. This process allows the incorporation of silicon pedestals that form series and shunt diodes or vias by imbedding them in a low loss, low dispersion glass. This hybrid combination of silicon and glass gives HMIC switches exceptional low loss and remarkable high isolation through low millimeter-wave frequencies.

Applications

These high performance switches are suitable for use in multi-band ECM, radar, and instrumentation control circuits where high isolation to insertion loss ratios are required. With a standard +5V/-5V, TTL controlled PIN diode driver, 50nS switching speeds are achieved.

Absolute Maximum Ratings

$T_{AMB} = +25^{\circ}\text{C}$ (Unless Otherwise Specified)

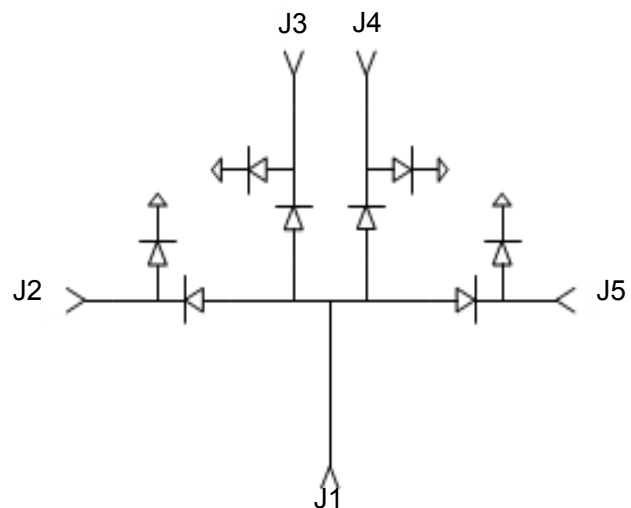
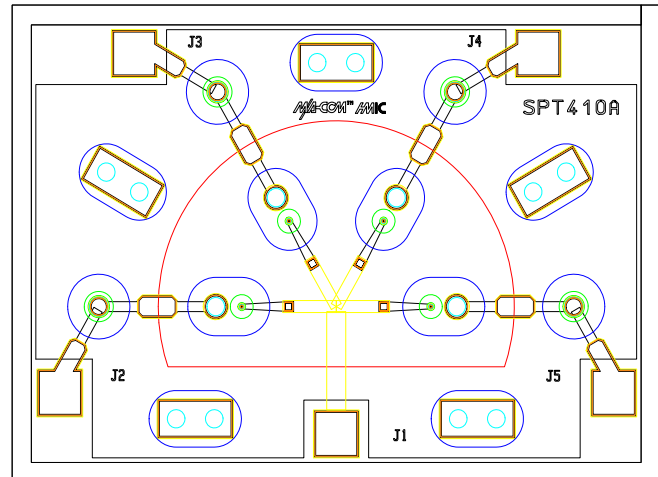
Parameter	Value
Operating Temperature	-65°C to +125°C
Storage Temperature	-65°C to +150°C
RF C.W. Incident Power (\pm 20mA)	+33dBm
Bias Current (Forward)	\pm 20mA
Applied Voltage (Reverse)	-25 Volts

Notes:

Exceeding these limits may cause permanent damage.

Maximum Operating Conditions for Combination of RF Power, D.C. Bias, and Temperature:

+30dBm C.W. @ 15 mA (per Diode) @ +85 °C.



Typical Driver Connections

Control Level (DC Current) at Port				Condition of RF Output	Condition of RF Output	Condition of RF Output	Condition of RF Output
J2	J3	J4	J5	J1-J2	J1-J3	J1-J4	J1-J5
-20mA	+20mA	+20mA	+20mA	Low Loss	Isolation	Isolation	Isolation
+20mA	-20mA	+20mA	+20mA	Isolation	Low Loss	Isolation	Isolation
+20mA	+20mA	-20mA	+20mA	Isolation	Isolation	Low Loss	Isolation
+20mA	+20mA	+20mA	-20mA	Isolation	Isolation	Isolation	Low Loss

Electrical Specifications @ T_{AMB} = +25°C, ± 20mA Bias Current (On-Wafer Measurements)

Parameter	Frequency	Minimum	Nominal	Maximum	Units
Insertion Loss	20 GHz		0.9	1.3	dB
Isolation	20 GHz	28	34		dB
Input Return Loss	20 GHz		15		dB
Output Return Loss	20 GHz		15		dB
Switching Speed ¹	10 GHz		50		nS

Notes:

Typical switching speed is measured from 10% to 90% of detected RF voltage driven by a TTL compatible driver. Driver output parallel RC network uses a capacitor between 390pF – 560pF and a resistor between 150Ω – 220Ω to achieve 50nS rise and fall times.

Operation of the MASW-004100-1193 PIN Switch

Operation of the MASW-004100-1193 PIN switch is achieved by the simultaneous application of negative DC current to the low loss port and positive DC current to the remaining isolated switching ports as shown in Figure 1. The backside area of the die is the RF and DC return ground plane. The DC return is achieved on the common port, J1. The DC control currents should be supplied by constant current source. The voltages at these points will not exceed ± 1.5 volts (1.2 volts typical) for supply currents up to ± 20 mA. In the low loss state, the series diode must be forward biased and the shunt diode reverse biased. For all the isolated ports, the shunt diode is forward biased and the series diode is reverse biased. The bias network design should yield > 30 dB RF to DC isolation.

Best insertion loss, P1dB, IP3, and switching speed are achieved by using a voltage pull-up resistor in the DC return path, J1. A minimum value of $-2V$ is recommended at this return node, which is achievable with a standard,

2 – 18 GHz Bias Network Schematic

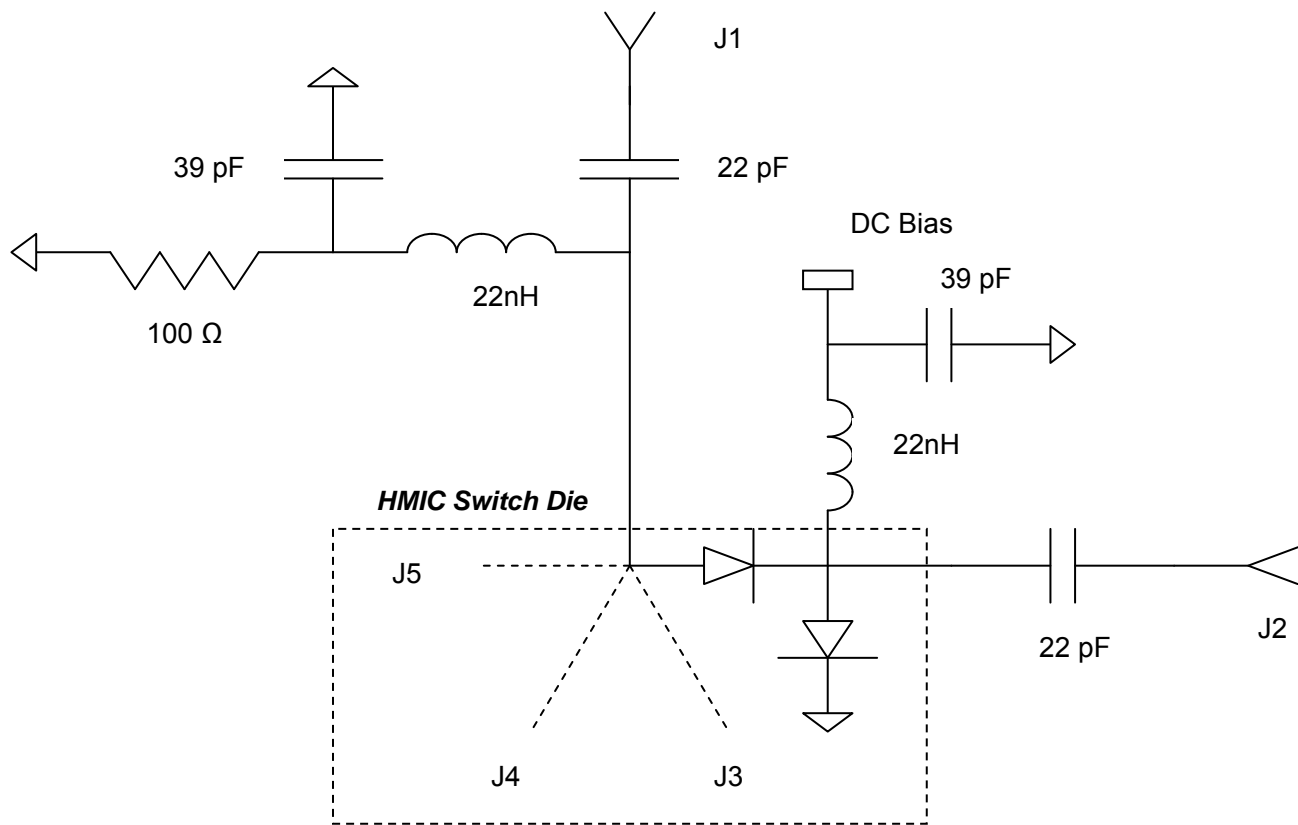
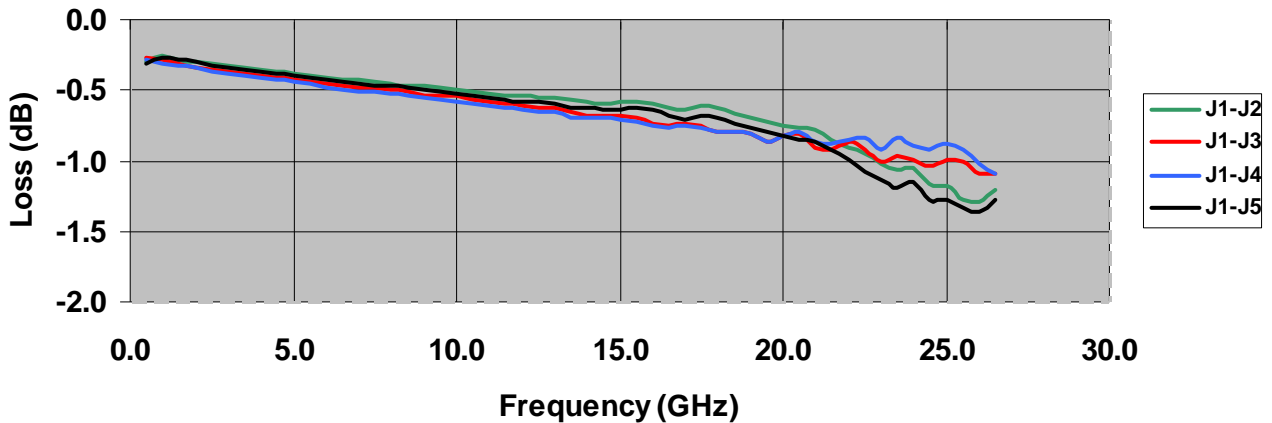


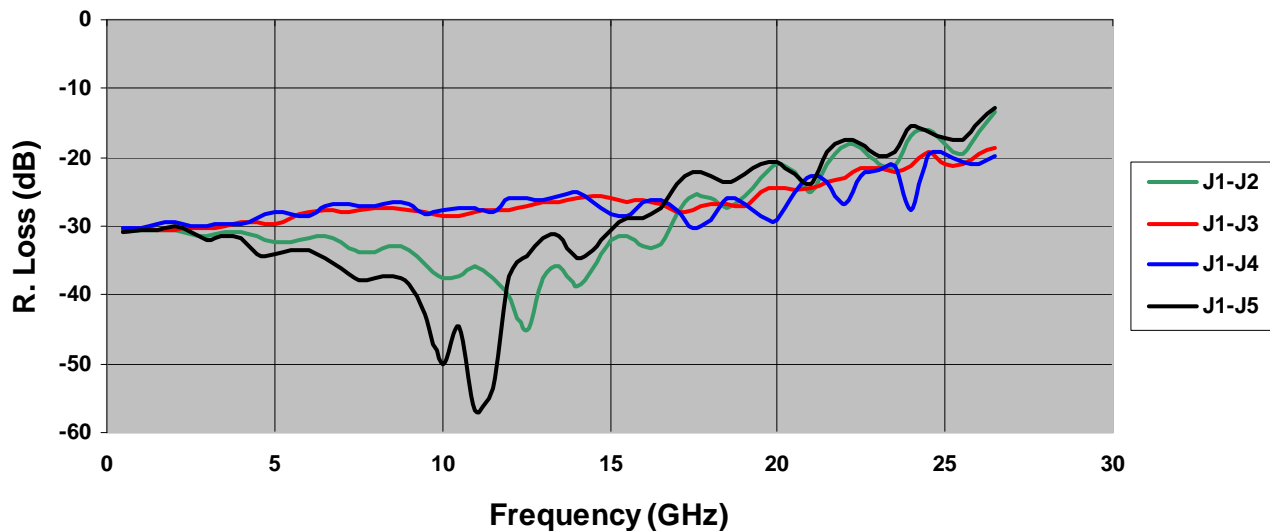
Fig. 1

Typical Microwave Performance

MASW-004100-1193 INSERTION LOSS

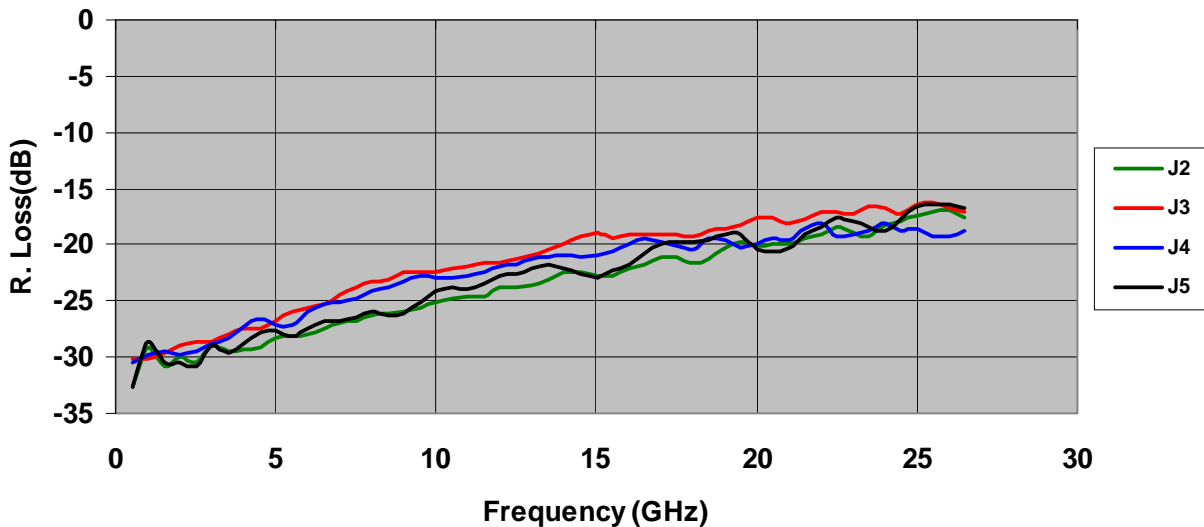


MASW-004100-1193 INPUT RETURN LOSS

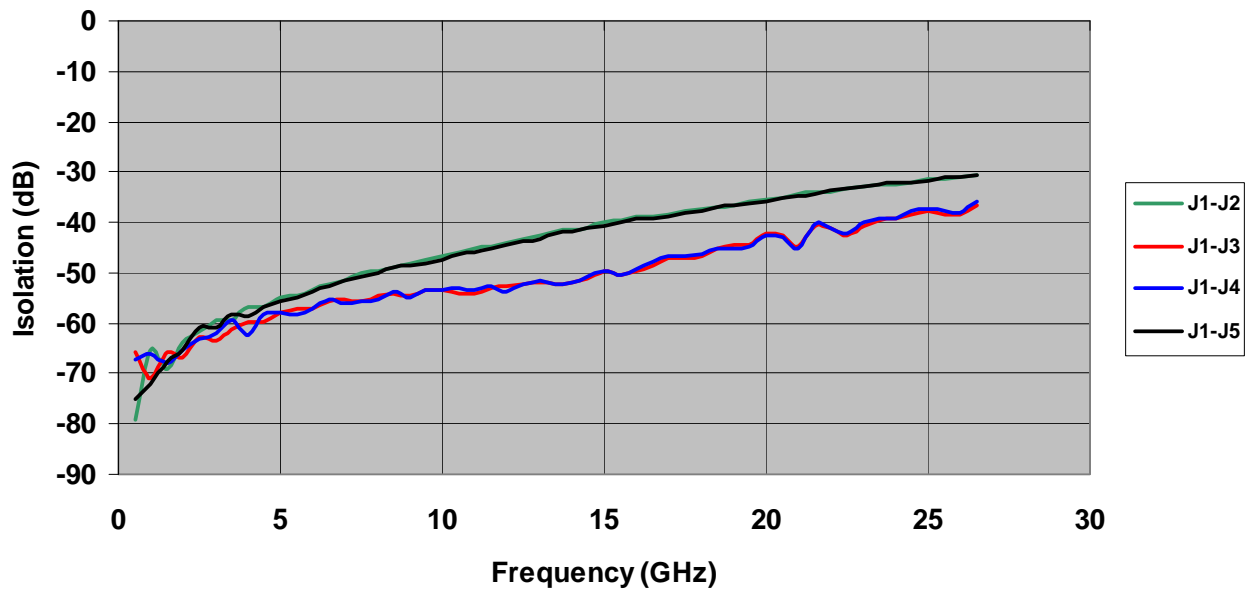


Typical Microwave Performance

MASW-004100-1193 OUTPUT RETURN LOSS



MASW-004100-1193 ISOLATION



ASSEMBLY INSTRUCTIONS

Cleanliness

These chips should be handled in a clean environment free of organic contamination.

Electro-Static Sensitivity

The MASW-00 Series PIN switches are ESD, Class 1A sensitive (HBM). The proper ESD handling procedures must be used.

Wire Bonding

Thermosonic wedge wire bonding using 0.003" x 0.00025" ribbon or 0.001" diameter gold wire is recommended. A stage temperature of 150°C and a force of 18 to 22 grams should be used. Ultrasonic energy should be adjusted to the minimum required to achieve a good bond. RF wire and ribbon bonds should be kept as short as possible to minimize parasitic inductance.

Mounting

These chips have Ti-Pt-Au back metal. They can be die mounted with a 80Au/20Sn or electrically conductive Ag epoxy. Mounting surface must be flat and clean of oils and contaminants.

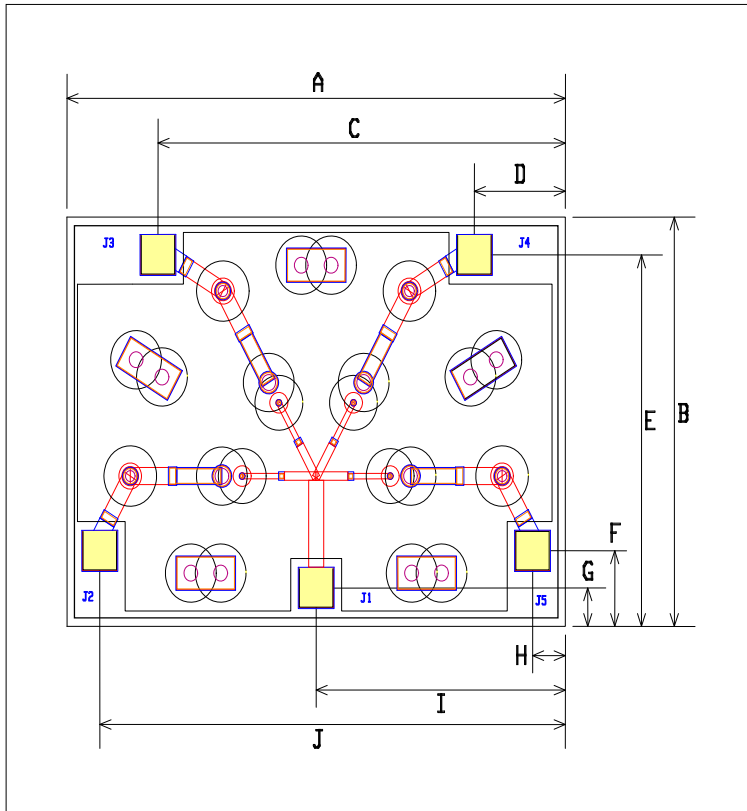
Eutectic Die Attachment

An 80/20 gold-tin eutectic solder preform is recommended with a work surface temperature of 255°C and a tool tip temperature of 265°C. When hot gas is applied, the tool tip temperature should be 290°C. The chip should not be exposed to temperatures greater than 320°C for more than 10 seconds. No more than 3 seconds should be required for the die attachment.

Silver Epoxy Die Attachment

Assembly should be preheated to 125°C-150°C. A Controlled thickness of 2 mils is recommended for best electrical and thermal conductivity. A thin epoxy fillet should be visible around the perimeter of the chip after placement to ensure complete coverage. Cure epoxy per manufacturer's recommended schedule.

MASW-004100-1193 Chip Dimensions



DIM	INCHES	MM
	NOMINAL	NOMINAL
A	.066	1.67
B	.047	1.19
C	.054	1.37
D	.012	0.31
E	.043	1.08
F	.009	0.22
G	.004	0.11
H	.004	0.11
I	.033	0.84
J	.061	1.56
Thickness	.005	.120
Bond Pads	.005X.005	0.120X.0120

Notes:

1. Topside and backside metallization is gold , 2.5mm thick typical.
2. Yellow areas indicate wire bonding pads

Ordering Information

Part Number	Package
MASW-004100-11930W	Waffle Pack
MASW-004100-11930G	Gel Pack